

Annex A: Measurement data and plots

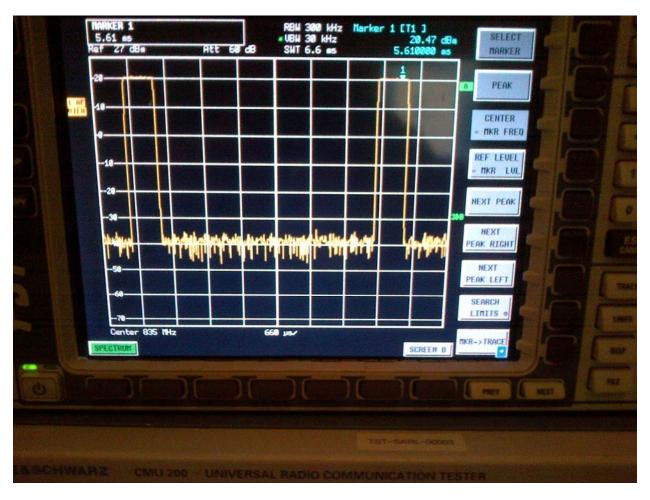
A.1 Spectrum analyser plots: GSM/UMTS, CW, 80%AM, signals



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Author Data **Daoud Attayi** Dates of Test
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Report No
RTS-6011-1208-40



GSM 835 MHz



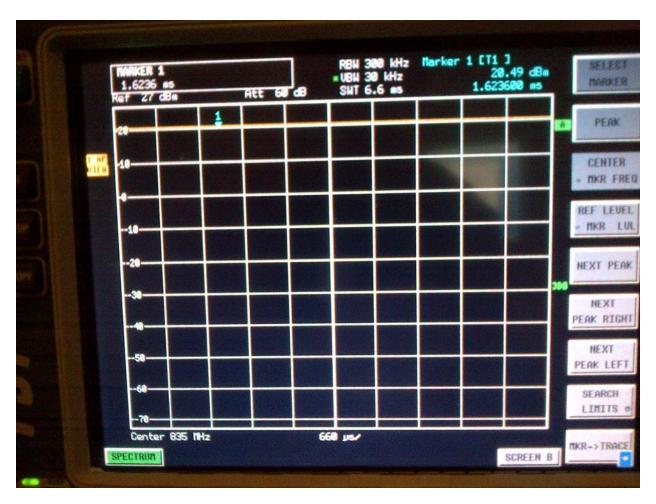
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Author Data **Daoud Attayi**

Dates of Test

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CW 835 MHz

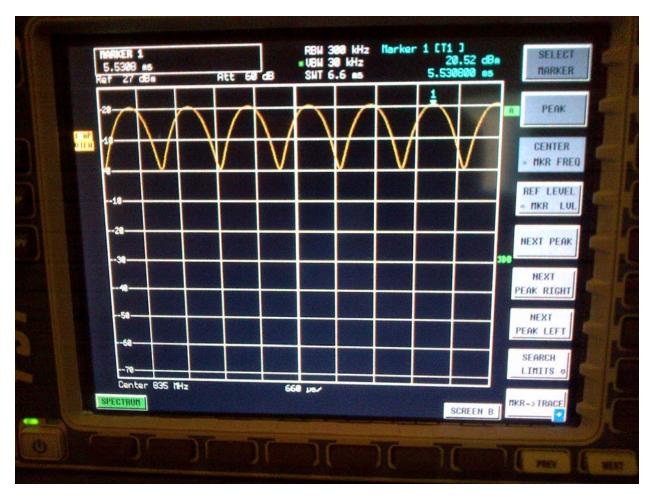


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Author Data **Daoud Attayi** Dates of Test

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AM 80% 835 MHz



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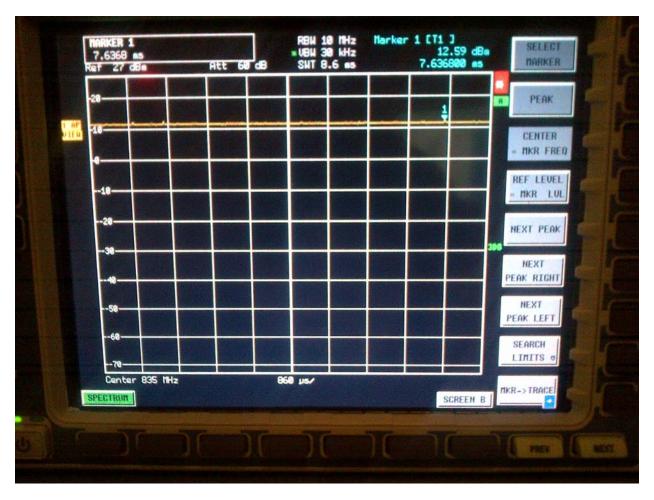
Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No **RTS-6011-1208-40**



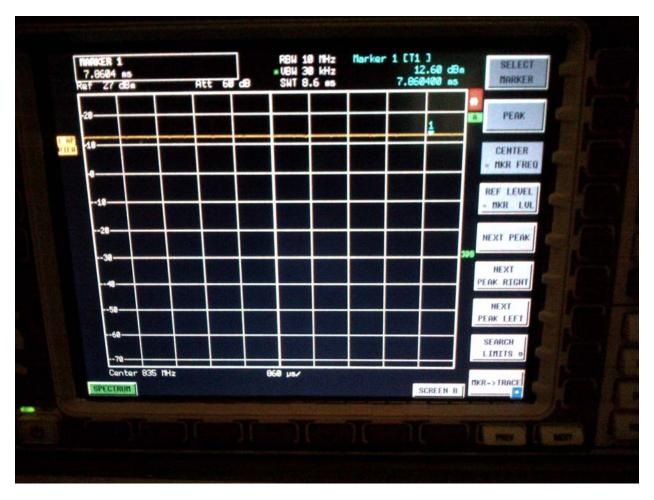
UMTS 835 MHz



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Author Data **Daoud Attayi** Dates of Test
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CW 835 MHz

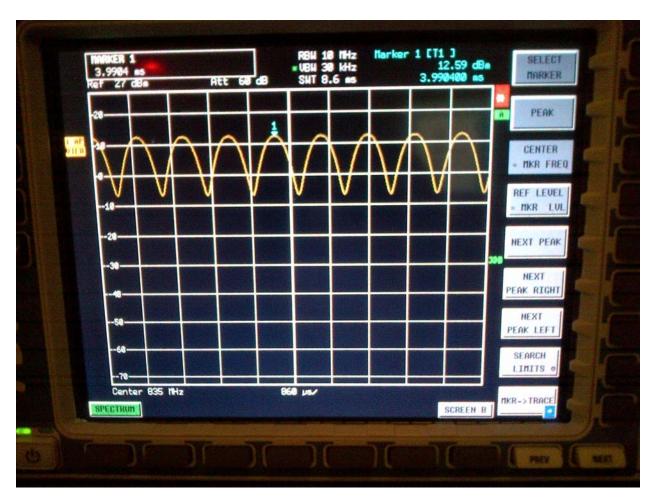


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Author Data **Daoud Attayi** Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40



AM 80% 835 MHz

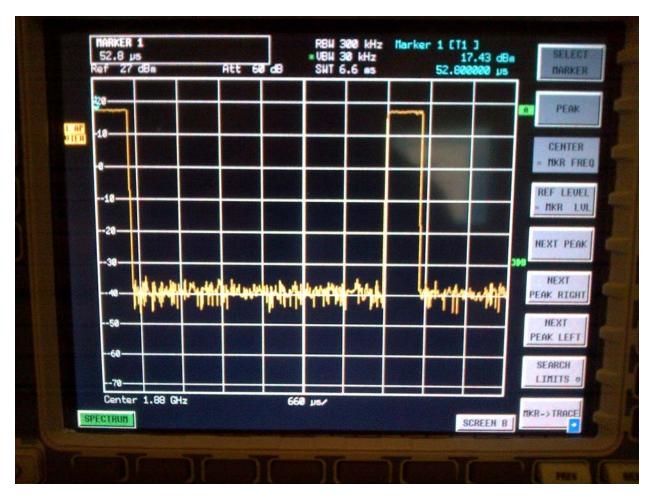


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Author Data **Daoud Attayi** Dates of Test

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GSM 1880 MHz

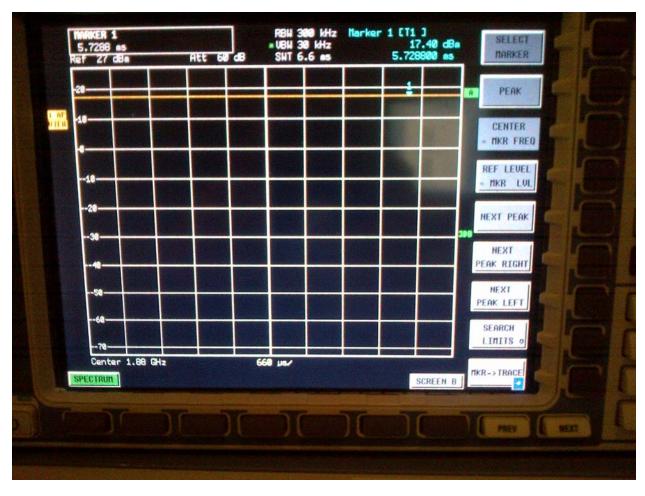


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Author Data **Daoud Attayi**

Dates of Test
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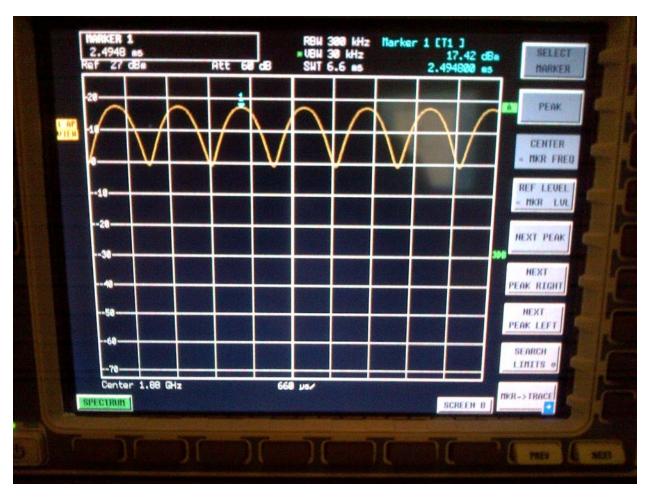
CW 1880 MHz



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AM 80 % 1880 MHz



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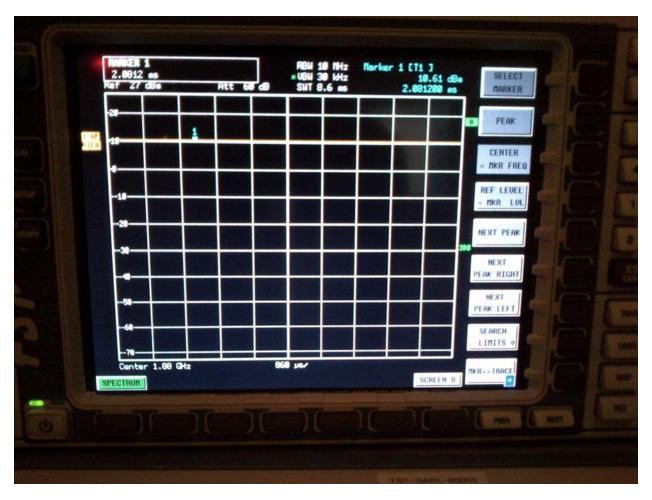
UMTS 1880 MHz



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Author Data **Daoud Attayi** Dates of Test
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CW 1880 MHz

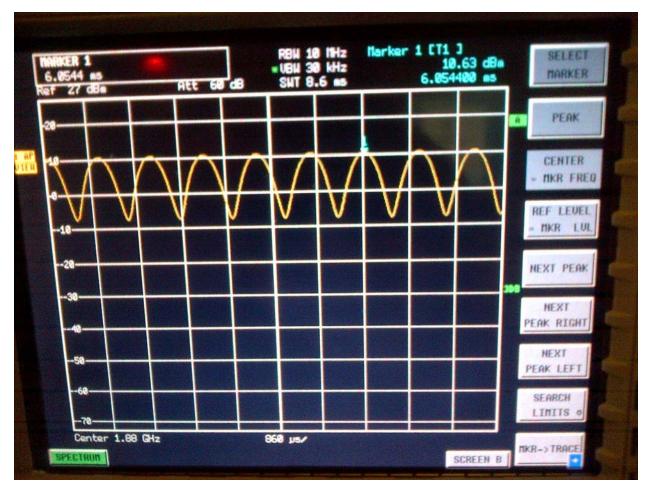


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Author Data **Daoud Attayi** Dates of Test

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AM 80 % 1880 MHz



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A.2 Dipole validation and probe modulation factor plots



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Author Data **Daoud Attayi**

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L6ARFG80UW

Date/Time: 6/1/2012 10:55:21 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_835 MHz_06_01_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 105.1 V/m; Power Drift = 0.15 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 163.0 V/m

Near-field category: M4 (AWF 0 dB)



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Author Data **Daoud Attayi** Dates of Test
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Report No
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FCC ID L6ARFG80UW

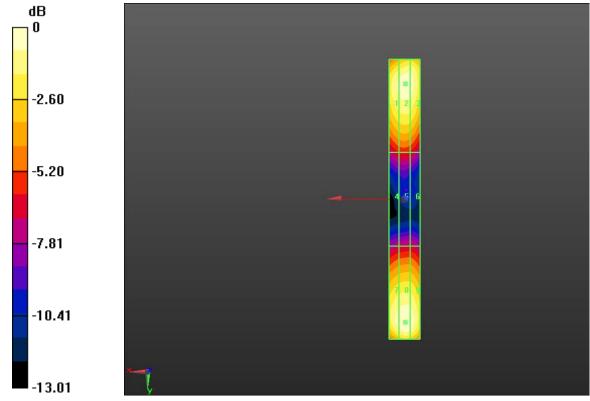
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
151.9 V/m	156.8 V/m	155.3 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
81.20 V/m	83.08 V/m	79.96 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
156.2 V/m	163.0 V/m	158.8 V/m

Cursor:

Total = 163.0 V/mE Category: M4

Location: -0.5, 79, 4.7 mm



0 dB = 163.0V/m = 44.24 dB V/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 1/31/2012 2:20:06 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM835 MHz_01_31_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835 PMF, Communication System: CW, Communication

System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 34.20 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 51.25 V/m

Near-field category: M4 (AWF 0 dB)



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L6ARFG80UW

FCC ID

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
46.59 V/m	49.14 V/m	49.14 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
27.62 V/m	28.27 V/m	28.03 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
49.67 V/m	51.25 V/m	50.67 V/m

Cursor:

Total = 51.249 V/m E Category: M4

Location: -0.5, 79.5, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 105.5 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 160.5 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
144.7 V/m	152.0 V/m	151.2 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
81.25 V/m	83.39 V/m	81.16 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
156.0 V/m	160.5 V/m	155.5 V/m



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Author Data

Daoud Attayi

Dates of Test

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Report No **RTS_6011_1208**

L6ARFG80UW

Cursor:

Total = 160.5 V/m E Category: M4 Location: 0, 79, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 67.40 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 101.2 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
90.33 V/m	95.24 V/m	95.16 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
51.51 V/m	53.10 V/m	51.99 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
97.22 V/m	101.2 V/m	98.82 V/m

Cursor:

Total = 101.2 V/m E Category: M4

Location: -0.5, 79, 4.7 mm



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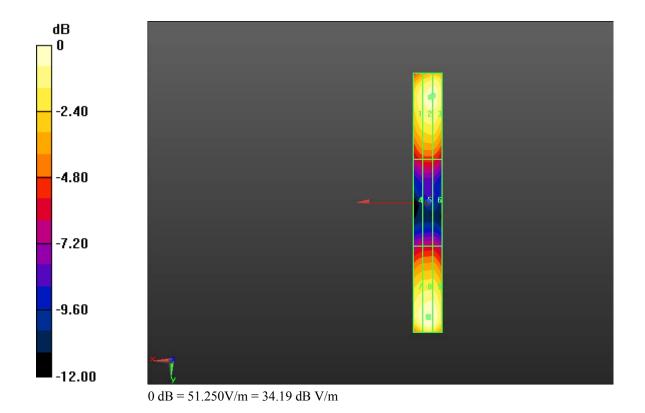
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Author Data **Daoud Attayi** Dates of Test

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 2/17/2012 12:24:15 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication

System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 41.08 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 64.41 V/m

Near-field category: M4 (AWF 0 dB)



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Author Data

Daoud Attayi

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PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
53.11 V/m	55.59 V/m	55.40 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
29.72 V/m	30.66 V/m	29.79 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
61.55 V/m	64.41 V/m	63.22 V/m

Cursor:

Total = 64.412 V/m E Category: M4

Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 43.11 V/m; Power Drift = -0.14 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 68.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
58.55 V/m	59.20 V/m	57.13 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
32.35 V/m	32.63 V/m	31.24 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
61.85 V/m	68.64 V/m	68.56 V/m



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Author Data

Daoud Attayi

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Report No **PTS_6011_1208**_

L6ARFG80UW

Cursor:

Total = 68.635 V/m E Category: M4

Location: -3, 79.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 28.41 V/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 45.21 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
38.28 V/m	38.73 V/m	37.25 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
21.72 V/m	21.89 V/m	20.80 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
40.90 V/m	45.21 V/m	45.16 V/m

Cursor:

Total = 45.209 V/m E Category: M4

Location: -3, 79.5, 4.7 mm



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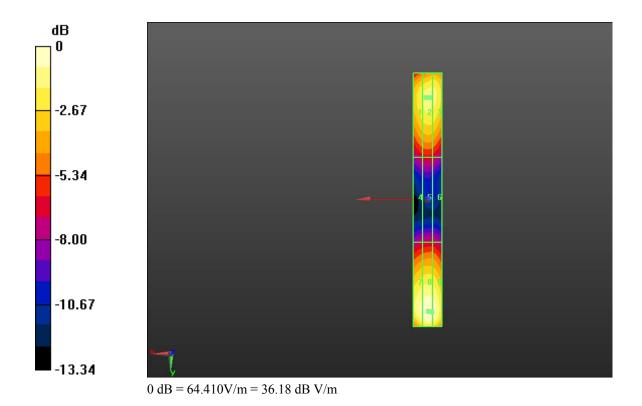
Author Data **Daoud Attayi**

Dates of Test

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Author Data **Daoud Attayi**

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L6ARFG80UW

Date/Time: 6/1/2012 10:48:59 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_1880 MHz_06_01_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 140.8 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 128.8 V/m

Near-field category: M2 (AWF 0 dB)



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FCC ID L6ARFG80UW

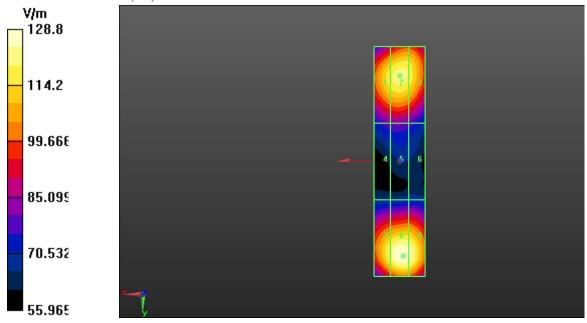
PMF scaled E-field

Grid 1 M2	Grid 2 M2	Grid 3 M2
118.3 V/m	121.5 V/m	118.8 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
81.24 V/m	82.44 V/m	79.52 V/m
Grid 7 M2	Grid 8 M2	Grid 9 M2
121.4 V/m	128.8 V/m	126.9 V/m

Cursor:

Total = 128.8 V/mE Category: M2

Location: -1.5, 37, 4.7 mm





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Author Data **Daoud Attavi**

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Report No

L6ARFG80UW

Date/Time: 1/31/2012 1:55:07 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM1880 MHz_01_31_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880, Communication System: CW, Communication System:

AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

• Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012

• Sensor-Surface: (Fix Surface), z = 4.7

• Electronics: DAE3 Sn472; Calibrated: 3/7/2011

• Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA

DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 34.29 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 30.95 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
27.89 V/m	29.29 V/m	29.22 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19.87 V/m	20.63 V/m	20.20 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
29.49 V/m	30.95 V/m	30.55 V/m



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Author Data **Daoud Attayi**

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Report No

L6ARFG80UW

Cursor:

Total = 30.947 V/mE Category: M4

Location: -1, 38, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 102.4 V/m; Power Drift = -0.11 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 90.42 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
82.60 V/m	86.68 V/m	86.04 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
58.55 V/m	60.47 V/m	58.89 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
85.63 V/m	90.42 V/m	88.30 V/m

Cursor:

Total = 90.419 V/mE Category: M3

Location: -0.5, 38, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing **Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.56 V/m; Power Drift = 0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 58.24 V/m

Near-field category: M4 (AWF 0 dB)



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Author Data **Daoud Attayi** Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

FCC ID L6ARFG80UW

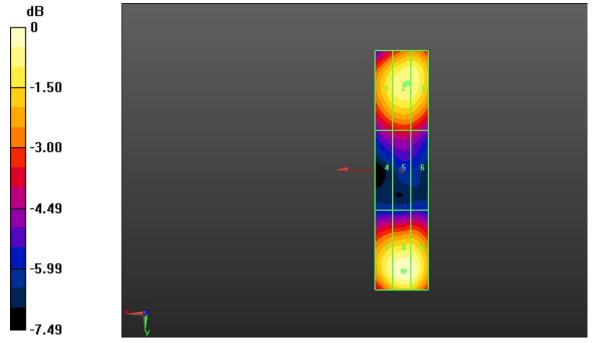
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
52.36 V/m	55.29 V/m	55.10 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
37.30 V/m	38.47 V/m	37.60 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
55.71 V/m	58.24 V/m	56.94 V/m

Cursor:

Total = 58.238 V/mE Category: M4

Location: -0.5, 38, 4.7 mm



0 dB = 30.950 V/m = 29.81 dB V/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 2/17/2012 2:20:23 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication

System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.02 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.43 V/m

Near-field category: M4 (AWF 0 dB)



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Author Data

Daoud Attayi

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40

L6ARFG80UW

FCC ID

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
37.98 V/m	39.42 V/m	39.04 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
26.86 V/m	27.50 V/m	26.70 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
39.63 V/m	42.43 V/m	41.87 V/m

Cursor:

Total = 42.427 V/m E Category: M4

Location: -1, 38, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.33 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
38.23 V/m	39.51 V/m	39.41 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
26.94 V/m	27.41 V/m	26.77 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
40.02 V/m	42.41 V/m	41.99 V/m



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 42.409 V/mE Category: M4

Location: -1.5, 38, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing **Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.18 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 27.40 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
24.40 V/m	25.26 V/m	24.95 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
17.20 V/m	17.65 V/m	1 7.12 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
25.54 V/m	27.40 V/m	27.02 V/m

Cursor:

Total = 27.402 V/mE Category: M4

Location: -1, 38, 4.7 mm



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW Page

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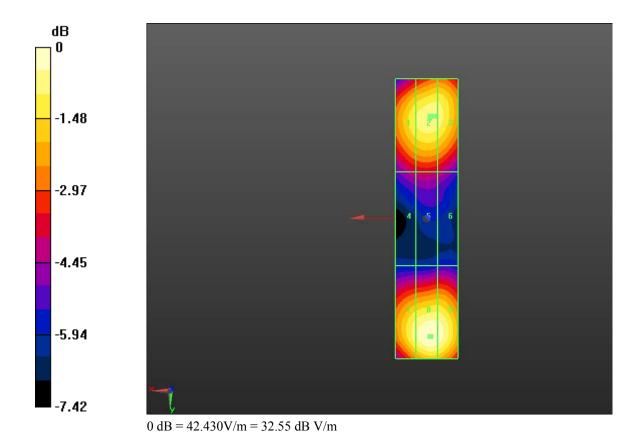
Author Data **Daoud Attayi**

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

REPORT NO

RTS-6011-1208-40





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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

CC ID

L6ARFG80UW

Date/Time: 6/1/2012 10:21:31 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_835 MHz_06_01_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.50 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.47 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data **Daoud Attayi** Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

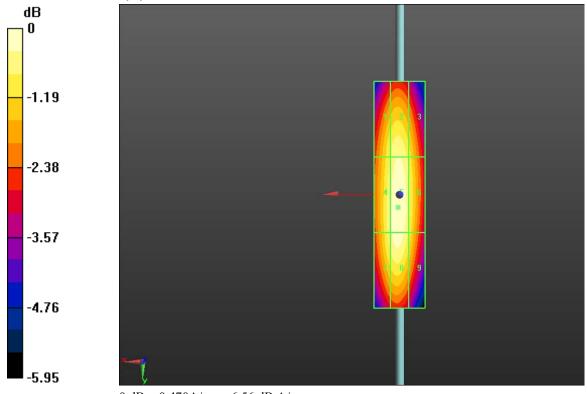
FCC ID L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.43 A/m	0.45 A/m	0.42 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.45 A/m	0.47 A/m	0.44 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.44 A/m	0.46 A/m	0.43 A/m

Cursor:

Total = 0.469 A/mH Category: M4 Location: 0.5, 5, 4.7 mm



0 dB = 0.470 A/m = -6.56 dB A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 1/31/2012 3:12:15 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM835 MHz_01_31_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835 PMF, Communication System: CW, Communication

System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - GSM 835 PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.17 V/m; Power Drift = -0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.16 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data
Daoud Attayi
Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012
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RTS-6

RTS-6011-1208-40

FCC ID L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.15 A/m	0.15 A/m	0.15 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.15 A/m	0.16 A/m	0.15 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.15 A/m	0.16 A/m	0.15 A/m

Cursor:

Total = 0.159 A/m H Category: M4 Location: 0, 1, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.27 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.47 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.43 A/m	0.45 A/m	0.43 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.45 A/m	0.47 A/m	0.45 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.44 A/m	0.46 A/m	0.43 A/m



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Author Data

Daoud Attayi

Dates of Test

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L6ARFG80UW

Cursor:

Total = 0.468 A/m H Category: M4 Location: 0, 4, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.32 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.30 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.28 A/m	0.29 A/m	0.27 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.29 A/m	0.30 A/m	0.28 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.28 A/m	0.30 A/m	0.28 A/m

Cursor:

Total = 0.302 A/m H Category: M4 Location: 0, 3.5, 4.7 mm



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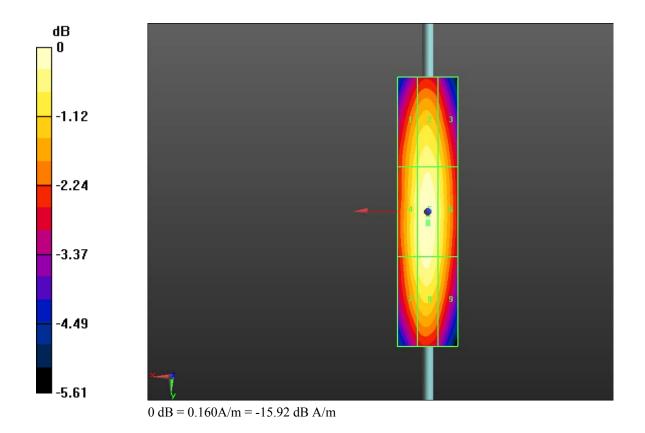
Author Data **Daoud Attayi** Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

REPORT NO

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FCC ID L6ARFG80UW





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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 2/17/2012 4:08:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication

System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.19 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.18 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40 FCC ID L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.16 A/m	0.17 A/m	0.16 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.17 A/m	0.18 A/m	0.17 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.17 A/m	0.18 A/m	0.17 A/m

Cursor:

Total = 0.181 A/m H Category: M4

Location: 0.5, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.11 V/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.20 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.17 A/m	0.19 A/m	0.18 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.18 A/m	0.20 A/m	0.19 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.18 A/m	0.19 A/m	0.18 A/m



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Author Data **Daoud Attayi**

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Report No

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Cursor:

Total = 0.197 A/mH Category: M4

Location: -0.5, 1, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.14 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.13 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.11 A/m	0.12 A/m	0.12 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.12 A/m	0.13 A/m	0.12 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.12 A/m	0.12 A/m	0.12 A/m

Cursor:

Total = 0.127 A/mH Category: M4

Location: 0, 1.5, 4.7 mm



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Author Data **Daoud Attayi**

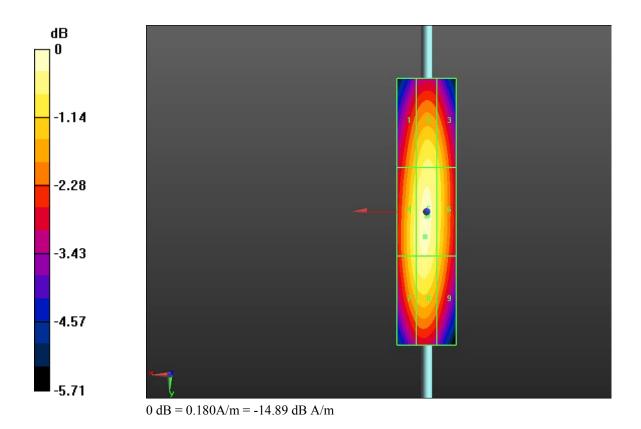
Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

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FCC ID L6ARFG80UW





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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 6/1/2012 10:29:55 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_1880 MHz_06_01_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid

Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.48 V/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.45 A/m

Near-field category: M2 (AWF 0 dB)



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Author Data **Daoud Attayi** Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

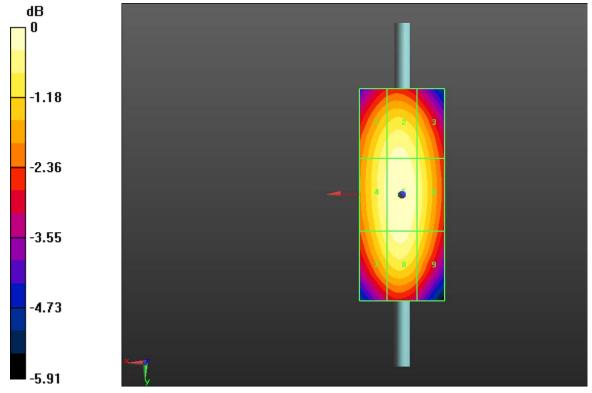
FCC ID L6ARFG80UW

PMF scaled H-field

Grid 1 M2	Grid 2 M2	Grid 3 M2
0.43 A/m	0.44 A/m	0.42 A/m
Grid 4 M2	Grid 5 M2	Grid 6 M2
0.44 A/m	0.45 A/m	0.43 A/m
Grid 7 M2	Grid 8 M2	Grid 9 M2
0.42 A/m	0.44 A/m	0.41 A/m

Cursor:

Total = 0.453 A/mH Category: M2 Location: 0.5, 0, 4.7 mm



0 dB = 0.450 A/m = -6.94 dB A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 1/31/2012 3:44:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM1880 MHz_01_31_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880 PMF, Communication System: CW, Communication

System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -GSM **1880_PMF/Hearing Aid Compatibility Test (41x101x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.12 V/m; Power Drift = -0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data **Daoud Attayi**

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Report No

L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.10 A/m	0.11 A/m	0.10 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.10 A/m	0.11 A/m	0.11 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.10 A/m	0.11 A/m	0.10 A/m

Cursor:

Total = 0.110 A/mH Category: M4

Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1800_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement

grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.35 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.33 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.30 A/m	0.32 A/m	0.31 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.31 A/m	0.33 A/m	0.31 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.30 A/m	0.32 A/m	0.30 A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

FCC ID L6ARFG80UW

Cursor:

Total = 0.327 A/mH Category: M3 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan -AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.23 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.21 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.20 A/m	0.21 A/m	0.20 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.20 A/m	0.21 A/m	0.20 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.20 A/m	0.21 A/m	0.20 A/m

Cursor:

Total = 0.214 A/mH Category: M3 Location: 0, 0, 4.7 mm



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW Page

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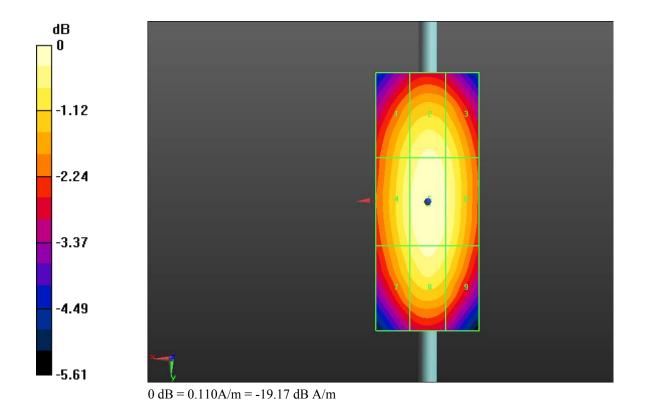
Author Data **Daoud Attayi** Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

REPORT NO

RTS-6011-1208-40

FCC ID L6ARFG80UW





Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 2/17/2012 3:56:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication

System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -UMTS **1880 PMF/Hearing Aid Compatibility Test (41x101x1):** Measurement grid: dx=5mm,

dv=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40 **Daoud Attayi**

Report No

L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.14 A/m	0.14 A/m	0.14 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.14 A/m	0.15 A/m	0.14 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.14 A/m	0.15 A/m	0.14 A/m

Cursor:

Total = 0.150 A/mH Category: M4 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement

grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.14 A/m	0.14 A/m	0.14 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.14 A/m	0.15 A/m	0.14 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.14 A/m	0.15 A/m	0.14 A/m



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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No RTS_6011_1208

L6ARFG80UW

Cursor:

Total = 0.149 A/m H Category: M4 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.10 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.10 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.09 A/m	0.09 A/m	0.09 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.09 A/m	0.10 A/m	0.09 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.09 A/m	0.09 A/m	0.09 A/m

Cursor:

Total = 0.096 A/m H Category: M4 Location: 0, 0, 4.7 mm



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Author Data **Daoud Attayi**

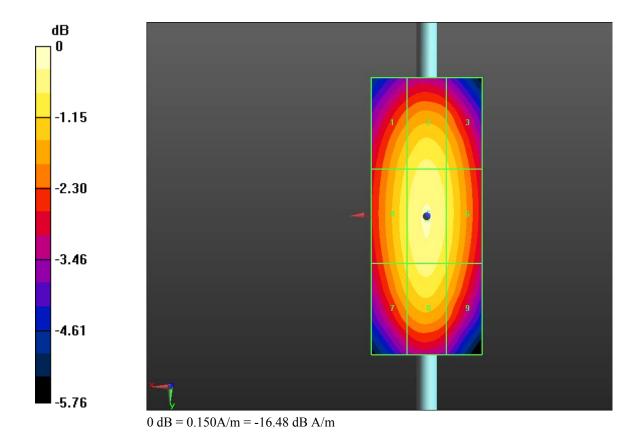
Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No

RTS-6011-1208-40

FCC ID L6ARFG80UW





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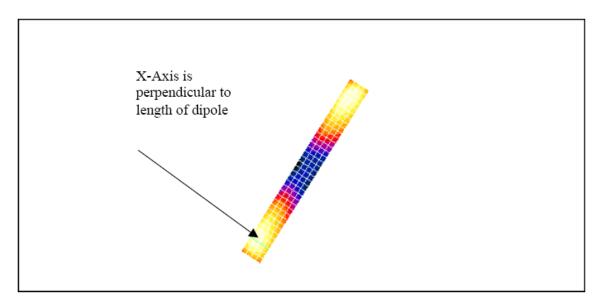
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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW



The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.



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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40

FCC ID L6ARFG80UW

Date/Time: 14/07/2005 11:35:24 AM Page 1 of 2

Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System; CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid :
123.2	138.1	138.4	123.2	138.1	138.
	Grid 5		Grid 4	Grid 5	Grid
80.9	92.3	92.2	80.9	92.3	92.2
	Grid 8		Grid 7		
119.8	131.0	130.7	119.8	131.0	130.

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW Page

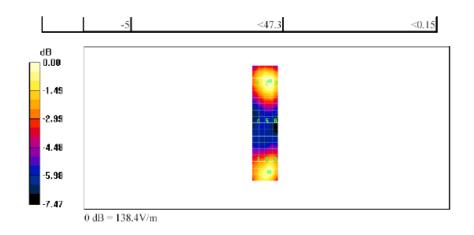
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Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40

FCC ID L6ARFG80UW

Date/Time: 14/07/2005 11:44:51 AM Page 1 of 2

Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System; CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 1000 kg/m³

Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid
123.1	138.6	138.6	123.1	138.6	138.
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid
81.4	92.1	91.6	81.4	92.1	91.6
Grid 7			Grid 7		
121.3	131.2	131.0	121.3	131.2	131.

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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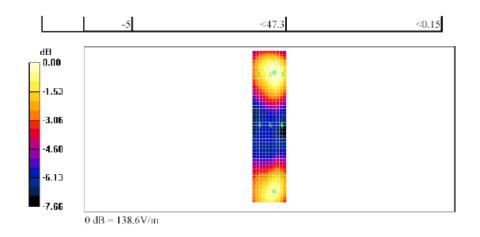
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Author Data **Daoud Attayi** Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012
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RTS-6011-1208-40

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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40 FCC ID L6ARFG80UW

Date/Time: 14/07/2005 12:43:02 PM Page 1 of 2

Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 1 kg/m³

Phantom section: H Dipole Section

DASY4 Configuration:

- Probe; H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.342	0.359	0.344	0.342	0.359	0.344
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.389	0.406	0.389	0.389	0.406	0.389
Grid 7	Grid 8	Grid 9			Grid 9
0.363	0.378	0.363	0.363	0.378	0.363

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



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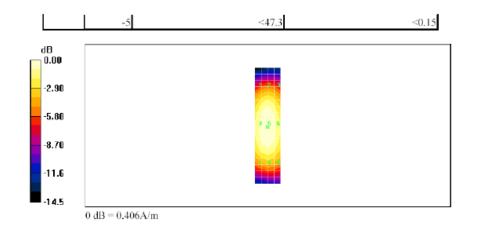
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Author Data **Daoud Attayi** Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

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Author Data

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Dates of Test

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Report No RTS-6011-1208-40

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Date/Time: 14/07/2005 12:53:40 PM Page 1 of 2

Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

						bac.
Grid 1	Grid 2	Grid 3		Grid 1	Grid 2	Grid 3
0.347	0.361	0.348		0.347	0.361	0.348
Grid 4	Grid 5	Grid 6		Grid 4	Grid 5	Grid 6
0.394	0.406	0.391		0.394	0.406	0.391
Grid 7				Grid 7	Grid 8	Grid 9
0.367	0.380	0.365		0.367	0.380	0.365

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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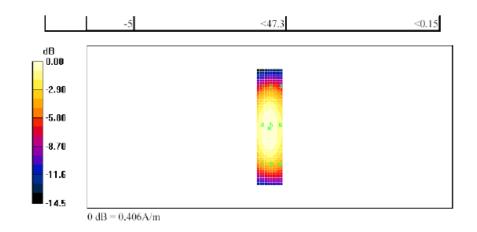
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Author Data **Daoud Attayi** Dates of Test
Jan. 31, Feb. 17, May 31-June 01, 2012 REPORT NO RTS-6011-1208-40

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Author Data **Daoud Attayi**

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

REPORT NO

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A.3 RF emission field plots



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Author Data

Daoud Attayi

Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 5/31/2012 8:04:24 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency:

848.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

• Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012

• Sensor-Surface: (Fix Surface), z = 8.7

• Electronics: DAE3 Sn473; Calibrated: 1/13/2012

• Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified

• DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 84.13 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 3.130 is applied.

E-field emissions = 205.5 V/m

Near-field category: M3 (AWF -5 dB)



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PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
176.7 V/m	192.4 V/m	188.3 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
191.0 V/m	205.5 V/m	199.1 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
208.9 V/m	217.7 V/m	201.1 V/m

Cursor:

Total = 217.7 V/mE Category: M3 Location: 1, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 98.57 V/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 3.130 is applied.

E-field emissions = 244.5 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
198.6 V/m	228.5 V/m	226.8 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
219.7 V/m	244.5 V/m	239.8 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
243.9 V/m	259.0 V/m	244.2 V/m



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 259.0 V/mE Category: M3 Location: 0, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 93.28 V/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 3.130 is applied.

E-field emissions = 226.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

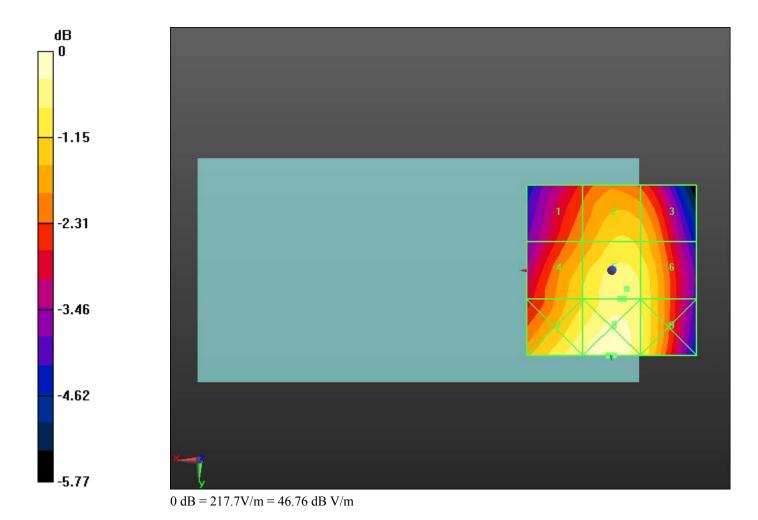
Grid 1 M3	Grid 2 M3	Grid 3 M3
190.9 V/m	220.0 V/m	217.0 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
202.0 V/m	226.9 V/m	222.0 V/m
Grid 7 M3 216.1 V/m	Grid 8 M3 230.9 V/m	Grid 9 M3 221.7 V/m

Cursor:

Total = 230.9 V/mE Category: M3

Location: -0.5, 25, 8.7 mm







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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Date/Time: 5/31/2012 9:47:11 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz,

Frequency: 846.6 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012

• Sensor-Surface: (Fix Surface), z = 8.7

• Electronics: DAE3 Sn473; Calibrated: 1/13/2012

Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified

DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device Low Chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 85.43 V/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 72.06 V/m

Near-field category: M4 (AWF 0 dB)



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
60.40 V/m	67.36 V/m	66.34 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
66.08 V/m	72.06 V/m	69.86 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
72.76 V/m	76.49 V/m	70.93 V/m

Cursor:

Total = 76.488 V/mE Category: M4

Location: 0.5, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 92.50 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 79.48 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
64.19 V/m	73.81 V/m	73.25 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
71.22 V/m	79.48 V/m	78.66 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
79.28 V/m	84.40 V/m	80.36 V/m



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW Page

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 84.399 V/mE Category: M4

Location: -1, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 103.8 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 87.99 V/m

Near-field category: M4 (AWF 0 dB)

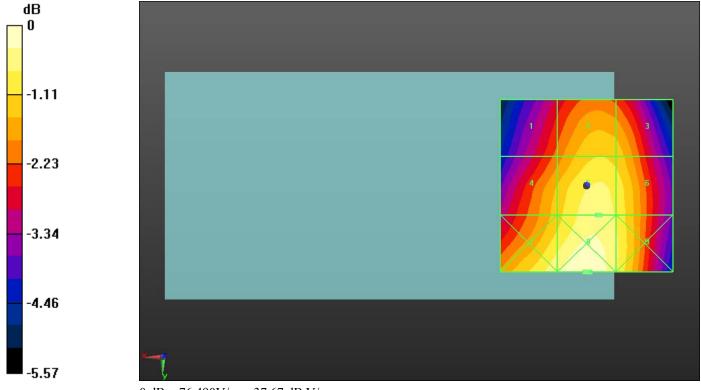
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
72.81 V/m	83.19 V/m	82.27 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
78.96 V/m	87.99 V/m	86.28 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
86.09 V/m	91.96 V/m	87.26 V/m

Cursor:

Total = 91.963 V/mE Category: M4 Location: 0, 25, 8.7 mm







Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 5/31/2012 9:24:49 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz,

Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.02 V/m; Power Drift = -0.09 dB

PMR not calibrated. PMF = 2.921 is applied.

E-field emissions = 60.76 V/m

Near-field category: M3 (AWF -5 dB)



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data **Daoud Attayi**

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Report No

L6ARFG80UW

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M4
60.76 V/m	53.30 V/m	42.58 V/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
43.99 V/m	59.74 V/m	60.63 V/m
Grid 7 M4	Grid 8 M3	Grid 9 M3
42.94 V/m	69.61 V/m	69.61 V/m

Cursor:

Total = 69.607 V/mE Category: M3

Location: -8, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.24 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 2.921 is applied.

E-field emissions = 76.83 V/m

Near-field category: M3 (AWF -5 dB)

Grid 1 M3	Grid 2 M3	Grid 3 M3
70.14 V/m	67.00 V/m	67.00 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
47.34 V/m	76.83 V/m	77.93 V/m
Grid 7 M4	Grid 8 M3	Grid 9 M3
42.92 V/m	79.74 V/m	80.22 V/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 80.218 V/mE Category: M3

Location: -10.5, 18.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.32 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 2.921 is applied.

E-field emissions = 51.67 V/m

Near-field category: M3 (AWF -5 dB)

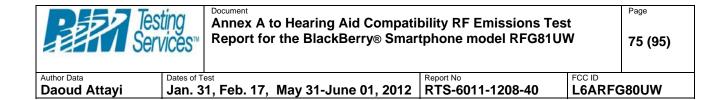
PMF scaled E-field

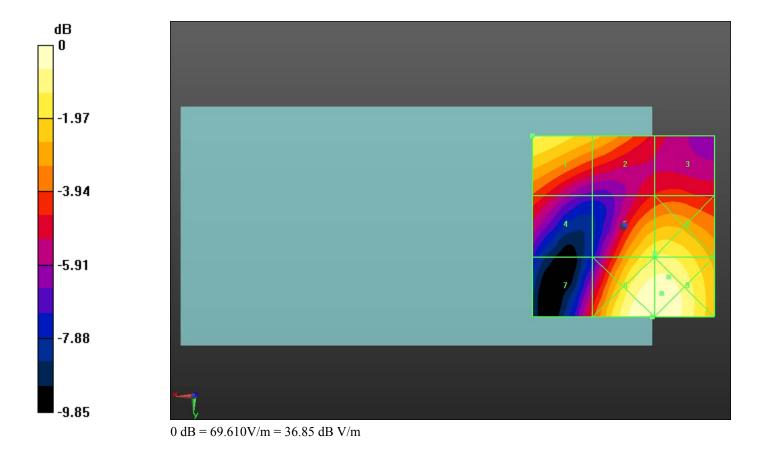
Grid 1 M3	Grid 2 M3	Grid 3 M3
50.34 V/m	49.29 V/m	49.14 V/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
40.02 V/m	51.67 V/m	52.97 V/m
Grid 7 M4	Grid 8 M3	Grid 9 M3
32.15 V/m	52.12 V/m	53.39 V/m

Cursor:

Total = 53.395 V/mE Category: M3

Location: -12.5, 14, 8.7 mm







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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 5/31/2012 10:17:04 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz,

Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.56 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 30.10 V/m

Near-field category: M4 (AWF 0 dB)



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Author Data **Daoud Attayi**

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Report No

L6ARFG80UW

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
29.76 V/m	27.33 V/m	22.41 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
20.87 V/m	30.10 V/m	30.65 V/m
Grid 7 M4 21.15 V/m	Grid 8 M4 35.00 V/m	Grid 9 M4 35.00 V/m

Cursor:

Total = 35.002 V/mE Category: M4

Location: -9, 24, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.36 V/m; Power Drift = -0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 28.30 V/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
27.22 V/m	23.85 V/m	24.34 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19.20 V/m	28.30 V/m	28.85 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
16.11 V/m	29.69 V/m	29.92 V/m



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Author Data **Daoud Attayi**

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Report No

L6ARFG80UW

Cursor:

Total = 29.915 V/mE Category: M4

Location: -10.5, 19, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 23.01 V/m; Power Drift = 0.02 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 24.04 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
23.60 V/m	21.71 V/m	22.22 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
18.18 V/m	24.04 V/m	24.72 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
14.31 V/m	24.43 V/m	25.00 V/m

Cursor:

Total = 24.999 V/mE Category: M4

Location: -12, 14.5, 8.7 mm



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Author Data **Daoud Attayi**

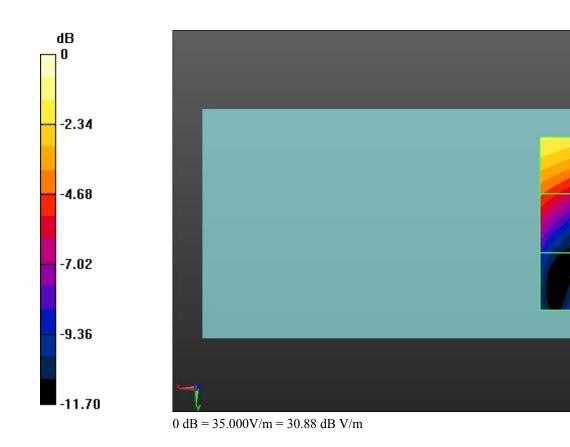
Dates of Test

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No

RTS-6011-1208-40

FCC ID L6ARFG80UW





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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 6/1/2012 12:16:55 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency:

848.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device low chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 2.940 is applied.

H-field emissions = 0.30 A/m

Near-field category: M4 (AWF -5 dB)



Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFG81UW

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Author Data

Daoud Attayi

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40

L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.40 A/m	0.30 A/m	0.20 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.37 A/m	0.27 A/m	0.18 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.39 A/m	0.27 A/m	0.17 A/m

Cursor:

Total = 0.402 A/m H Category: M4

Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09 V/m; Power Drift = 0.09 dB

PMR not calibrated. PMF = 2.940 is applied.

H-field emissions = 0.37 A/m

Near-field category: M4 (AWF -5 dB)

Grid 1 M3	Grid 2 M4	Grid 3 M4
0.50 A/m	0.37 A/m	0.25 A/m
Grid 4 M3	Grid 5 M4	Grid 6 M4
0.46 A/m	0.34 A/m	0.22 A/m
Grid 7 M3	Grid 8 M4	Grid 9 M4
0.49 A/m	0.35 A/m	0.22 A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 0.503 A/mH Category: M3

Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.10 V/m; Power Drift = 0.05 dBPMR not calibrated. PMF = 2.940 is applied. H-field emissions = 0.38 A/m

Near-field category: M4 (AWF -5 dB)

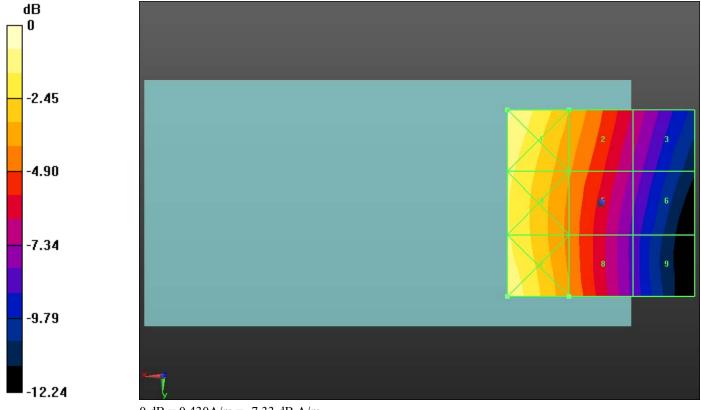
PMF scaled H-field

Grid 1 M3	Grid 2 M4	Grid 3 M4
0.50 A/m	0.37 A/m	0.25 A/m
Grid 4 M3	Grid 5 M4	Grid 6 M4
0.47 A/m	0.35 A/m	0.24 A/m
Grid 7 M3	Grid 8 M4	Grid 9 M4
0.52 A/m	0.38 A/m	0.25 A/m

Cursor:

Total = 0.518 A/mH Category: M3 Location: 25, 25, 8.7 mm





0 dB = 0.430 A/m = -7.33 dB A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 5/31/2012 11:38:02 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz,

Frequency: 846.6 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011

Sensor-Surface: (Fix Surface), z = 8.7

• Electronics: DAE3 Sn473; Calibrated: 1/13/2012

Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified

• DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device low chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07 V/m; Power Drift = -0.02 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)



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Author Data

Daoud Attayi

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L6ARFG80UW

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.14 A/m	0.11 A/m	0.07 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.13 A/m	0.10 A/m	0.06 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.15 A/m	0.11 A/m	0.07 A/m

Cursor:

Total = 0.148 A/m H Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.12 A/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.16 A/m	0.12 A/m	0.08 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.15 A/m	0.11 A/m	0.07 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.17 A/m	0.12 A/m	0.07 A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

Report No

L6ARFG80UW

Cursor:

Total = 0.165 A/mH Category: M4

Location: 25, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.10 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

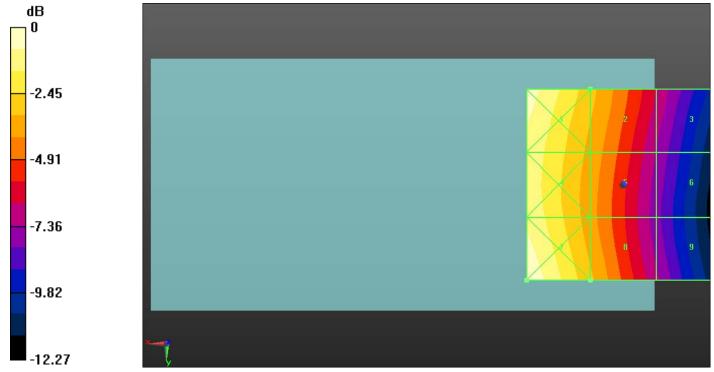
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.19 A/m	0.14 A/m	0.10 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.18 A/m	0.14 A/m	0.09 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.20 A/m	0.15 A/m	0.09 A/m

Cursor:

Total = 0.200 A/mH Category: M4

Location: 25, 25, 8.7 mm

Test Serv	ting ⁄ices™	Annex A to Hearing Aid Compati Report for the BlackBerry® Smar			Page 87 (95)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi	Jan. 3	1, Feb. 17, May 31-June 01, 2012	RTS-6011-1208-40	L6ARFG	WU08



0 dB = 0.150A/m = -16.48 dB A/m



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Author Data **Daoud Attayi**

Jan. 31, Feb. 17, May 31-June 01, 2012 RTS-6011-1208-40

L6ARFG80UW

Date/Time: 6/1/2012 12:33:46 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz,

Frequency: 1909.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011

Sensor-Surface: (Fix Surface), z = 8.7

• Electronics: DAE3 Sn473; Calibrated: 1/13/2012

Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified

• DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device low chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06 V/m; Power Drift = 0.20 dB

PMR not calibrated. PMF = 2.970 is applied.

H-field emissions = 0.17 A/m

Near-field category: M3 (AWF -5 dB)



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Author Data

Daoud Attayi

Jan. 31, Feb. 17, May 31-June 01, 2012

Report No RTS-6011-1208-40

L6ARFG80UW

PMF scaled H-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.16 A/m	0.17 A/m	0.17 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.16 A/m	0.17 A/m	0.17 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M4
0.18 A/m	0.17 A/m	0.14 A/m

Cursor:

Total = 0.178 A/m H Category: M3

Location: 18.5, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 2.970 is applied.

H-field emissions = 0.23 A/m

Near-field category: M3 (AWF -5 dB)

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.23 A/m	0.22 A/m	0.21 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.21 A/m	0.22 A/m	0.20 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.23 A/m	0.22 A/m	0.18 A/m



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Cursor:

Total = 0.232 A/mH Category: M3

Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06 V/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 2.970 is applied.

H-field emissions = 0.20 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.20 A/m	0.18 A/m	0.16 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.18 A/m	0.18 A/m	0.16 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.17 A/m	0.17 A/m	0.14 A/m

Cursor:

Total = 0.195 A/mH Category: M3

Location: 25, -25, 8.7 mm



-1.21 -2.42 -3.64 -4.85

0 dB = 0.170 A/m = -15.39 dB A/m

-6.06



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Date/Time: 5/31/2012 11:23:23 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample; Serial: 2A099B03

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz,

Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device low chan/Hearing Aid Compatibility Test

(**101x101x1**): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = 0.07 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08 A/m

Near-field category: M4 (AWF 0 dB)



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PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.08 A/m	0.08 A/m	0.08 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.08 A/m	0.08 A/m	0.08 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.09 A/m	0.08 A/m	0.07 A/m

Cursor:

Total = 0.088 A/m H Category: M4

Location: 19.5, 25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08 A/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.08 A/m	0.08 A/m	0.08 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.07 A/m	0.08 A/m	0.07 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.08 A/m	0.08 A/m	0.06 A/m



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Cursor:

Total = 0.083 A/mH Category: M4

Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = -0.12 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.08 A/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.08 A/m	0.08 A/m	0.07 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.07 A/m	0.07 A/m	0.07 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.08 A/m	0.07 A/m	0.06 A/m

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